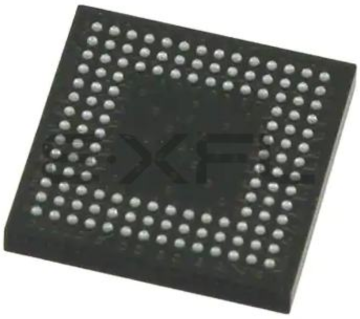

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

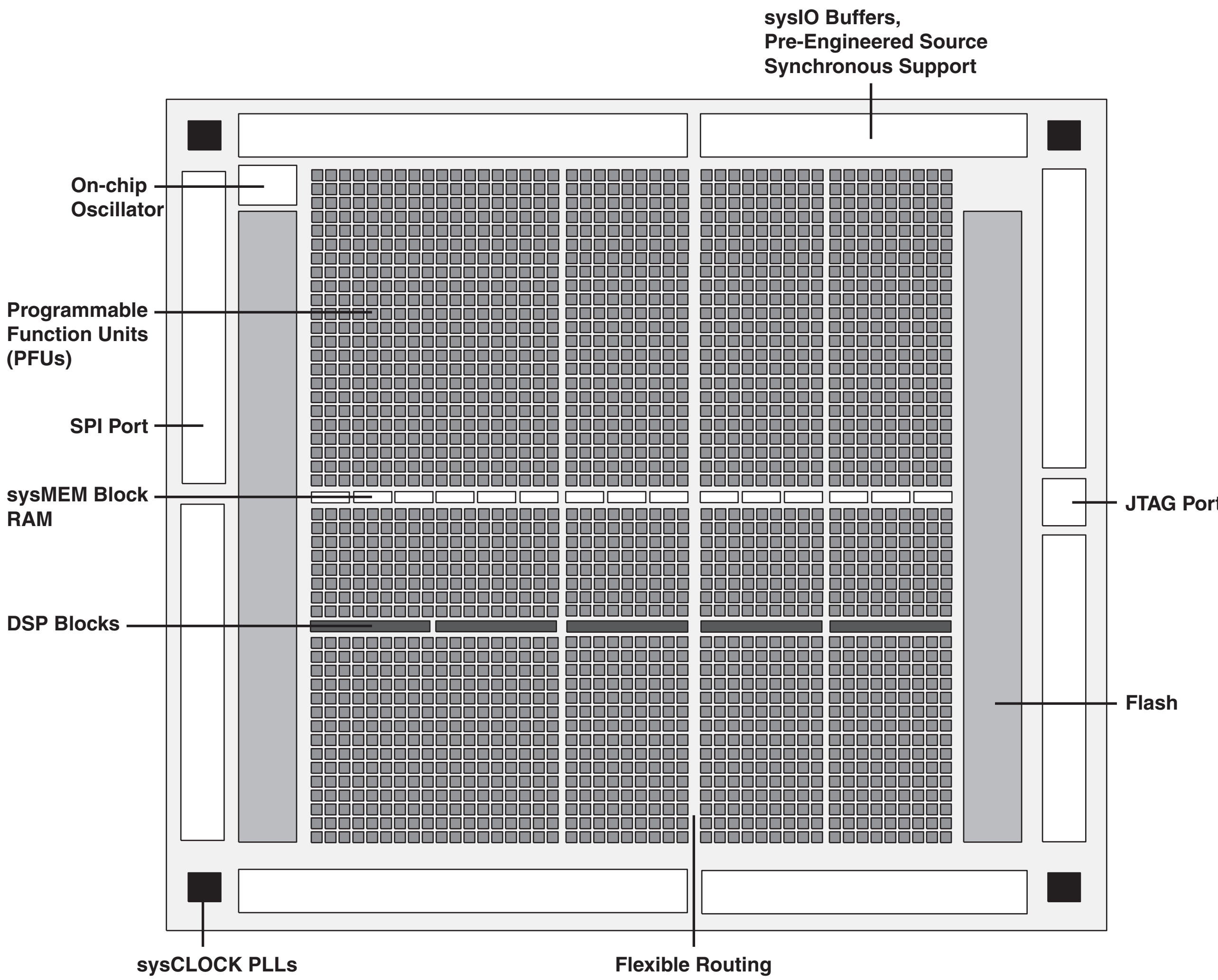
Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	625
Number of Logic Elements/Cells	5000
Total RAM Bits	169984
Number of I/O	86
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	132-LFBGA, CSPBGA
Supplier Device Package	132-CSBGA (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfxp2-5e-5m132c

Figure 2-1. Simplified Block Diagram, LatticeXP2-17 Device (Top Level)

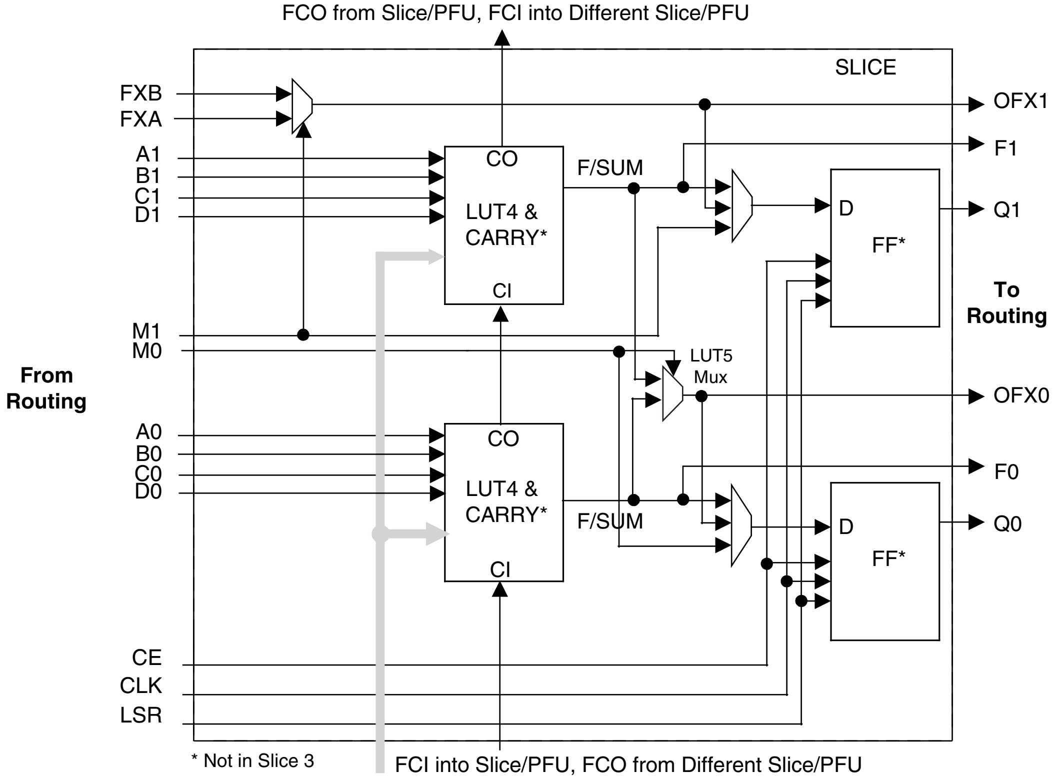


PFU Blocks

The core of the LatticeXP2 device is made up of logic blocks in two forms, PFUs and PFFs. PFUs can be programmed to perform logic, arithmetic, distributed RAM and distributed ROM functions. PFF blocks can be programmed to perform logic, arithmetic and ROM functions. Except where necessary, the remainder of this data sheet will use the term PFU to refer to both PFU and PFF blocks.

Each PFU block consists of four interconnected slices, numbered Slice 0 through Slice 3, as shown in Figure 2-2. All the interconnections to and from PFU blocks are from routing. There are 50 inputs and 23 outputs associated with each PFU block.

Figure 2-3. Slice Diagram



For Slices 0 and 2, memory control signals are generated from Slice 1 as follows:
WCK is CLK
WRE is from LSR
DI[3:2] for Slice 2 and DI[1:0] for Slice 0 data
WAD [A:D] is a 4bit address from slice 1 LUT input

Table 2-2. Slice Signal Descriptions

Function	Type	Signal Names	Description
Input	Data signal	A0, B0, C0, D0	Inputs to LUT4
Input	Data signal	A1, B1, C1, D1	Inputs to LUT4
Input	Multi-purpose	M0	Multipurpose Input
Input	Multi-purpose	M1	Multipurpose Input
Input	Control signal	CE	Clock Enable
Input	Control signal	LSR	Local Set/Reset
Input	Control signal	CLK	System Clock
Input	Inter-PFU signal	FCI	Fast Carry-In[1]
Input	Inter-slice signal	FXA	Intermediate signal to generate LUT6 and LUT7
Input	Inter-slice signal	FXB	Intermediate signal to generate LUT6 and LUT7
Output	Data signals	F0, F1	LUT4 output register bypass signals
Output	Data signals	Q0, Q1	Register outputs
Output	Data signals	OFX0	Output of a LUT5 MUX
Output	Data signals	OFX1	Output of a LUT6, LUT7, LUT8[2] MUX depending on the slice
Output	Inter-PFU signal	FCO	Slice 2 of each PFU is the fast carry chain output[1]

1. See Figure 2-3 for connection details.
2. Requires two PFUs.

Figure 2-4. General Purpose PLL (GPLL) Diagram

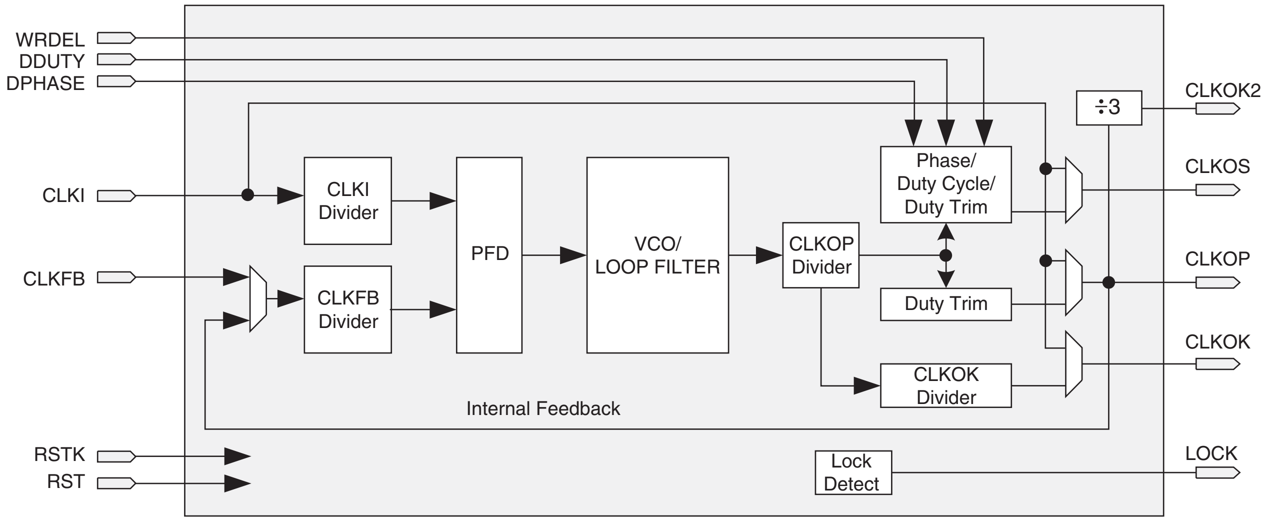


Table 2-4 provides a description of the signals in the GPLL blocks.

Table 2-4. GPLL Block Signal Descriptions

Signal	I/O	Description
CLKI	I	Clock input from external pin or routing
CLKFB	I	PLL feedback input from CLKOP (PLL internal), from clock net (CLKOP) or from a user clock (PIN or logic)
RST	I	“1” to reset PLL counters, VCO, charge pumps and M-dividers
RSTK	I	“1” to reset K-divider
DPHASE [3:0]	I	DPA Phase Adjust input
DDDUTY [3:0]	I	DPA Duty Cycle Select input
WRDEL	I	DPA Fine Delay Adjust input
CLKOS	O	PLL output clock to clock tree (phase shifted/duty cycle changed)
CLKOP	O	PLL output clock to clock tree (no phase shift)
CLKOK	O	PLL output to clock tree through secondary clock divider
CLKOK2	O	PLL output to clock tree (CLKOP divided by 3)
LOCK	O	“1” indicates PLL LOCK to CLKI

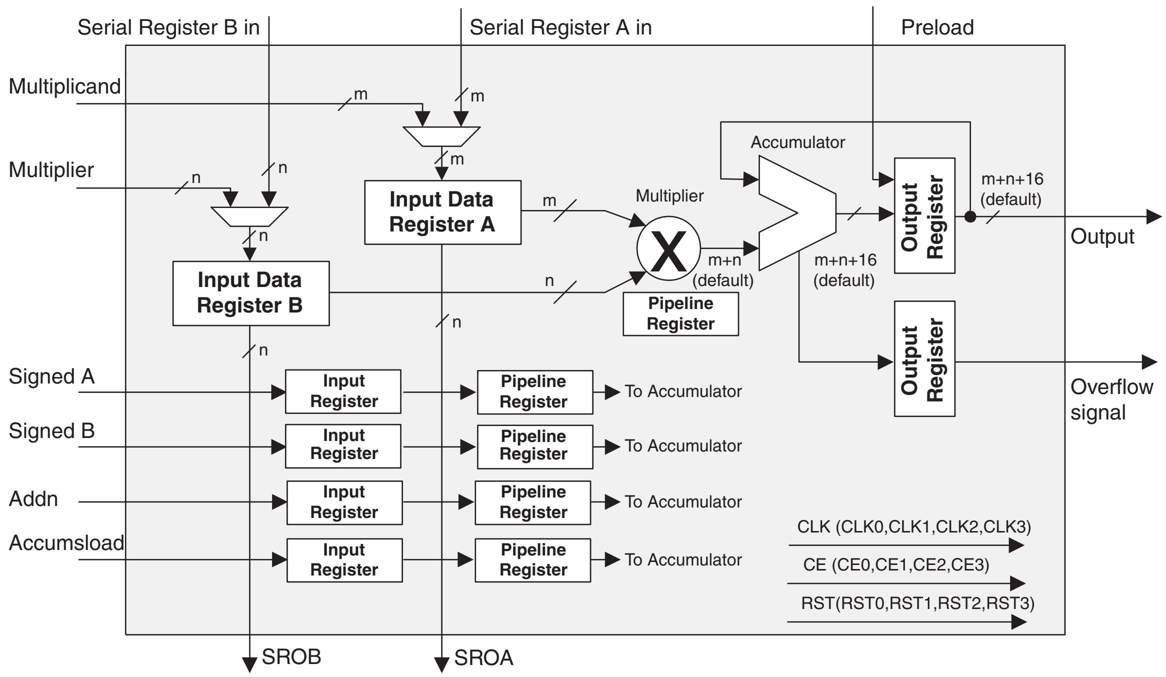
Clock Dividers

LatticeXP2 devices have two clock dividers, one on the left side and one on the right side of the device. These are intended to generate a slower-speed system clock from a high-speed edge clock. The block operates in a ÷2, ÷4 or ÷8 mode and maintains a known phase relationship between the divided down clock and the high-speed clock based on the release of its reset signal. The clock dividers can be fed from the CLKOP output from the GPLLs or from the Edge Clocks (ECLK). The clock divider outputs serve as primary clock sources and feed into the clock distribution network. The Reset (RST) control signal resets the input and forces all outputs to low. The RELEASE signal releases outputs to the input clock. For further information on clock dividers, please see TN1126, LatticeXP2 sysCLOCK PLL Design and Usage Guide. Figure 2-5 shows the clock divider connections.

MAC sysDSP Element

In this case, the two operands, A and B, are multiplied and the result is added with the previous accumulated value. This accumulated value is available at the output. The user can enable the input and pipeline registers but the output register is always enabled. The output register is used to store the accumulated value. The Accumulators in the DSP blocks in LatticeXP2 family can be initialized dynamically. A registered overflow signal is also available. The overflow conditions are provided later in this document. Figure 2-21 shows the MAC sysDSP element.

Figure 2-21. MAC sysDSP



MULTADDSUB sysDSP Element

In this case, the operands A0 and B0 are multiplied and the result is added/subtracted with the result of the multiplier operation of operands A1 and B1. The user can enable the input, output and pipeline registers. Figure 2-22 shows the MULTADDSUB sysDSP element.

Figure 2-22. MULTADDSUB

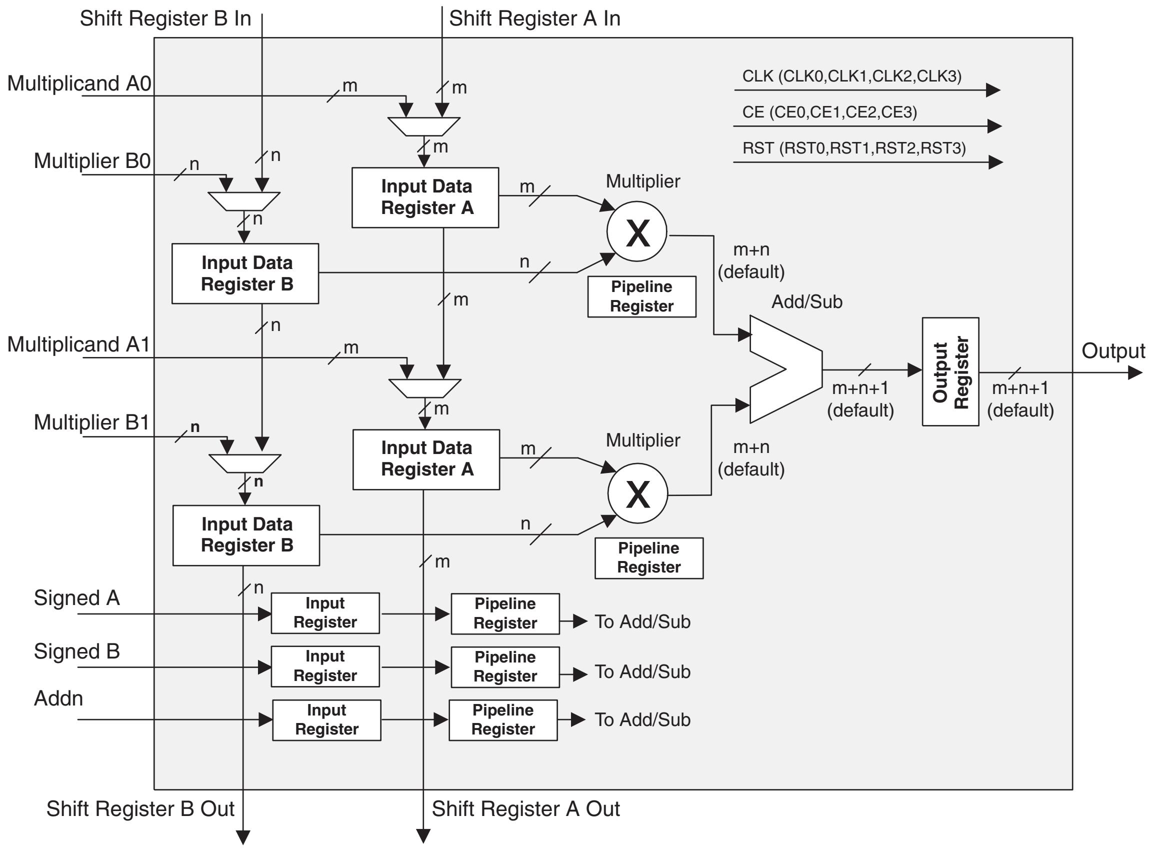


Table 2-11. PIO Signal List

Name	Type	Description
CE	Control from the core	Clock enables for input and output block flip-flops
CLK	Control from the core	System clocks for input and output blocks
ECLK1, ECLK2	Control from the core	Fast edge clocks
LSR	Control from the core	Local Set/Reset
GSRN	Control from routing	Global Set/Reset (active low)
INCK[2]	Input to the core	Input to Primary Clock Network or PLL reference inputs
DQS	Input to PIO	DQS signal from logic (routing) to PIO
INDD	Input to the core	Unregistered data input to core
INFF	Input to the core	Registered input on positive edge of the clock (CLK0)
IPOS0, IPOS1	Input to the core	Double data rate registered inputs to the core
QPOS0[1], QPOS1[1]	Input to the core	Gearbox pipelined inputs to the core
QNEG0[1], QNEG1[1]	Input to the core	Gearbox pipelined inputs to the core
OPOS0, ONEG0, OPOS2, ONEG2	Output data from the core	Output signals from the core for SDR and DDR operation
OPOS1 ONEG1	Tristate control from the core	Signals to Tristate Register block for DDR operation
DEL[3:0]	Control from the core	Dynamic input delay control bits
TD	Tristate control from the core	Tristate signal from the core used in SDR operation
DDRCLKPOL	Control from clock polarity bus	Controls the polarity of the clock (CLK0) that feed the DDR input block
DQSXFER	Control from core	Controls signal to the Output block

1. Signals available on left/right/bottom only.
2. Selected I/O.

PIO

The PIO contains four blocks: an input register block, output register block, tristate register block and a control logic block. These blocks contain registers for operating in a variety of modes along with necessary clock and selection logic.

Input Register Block

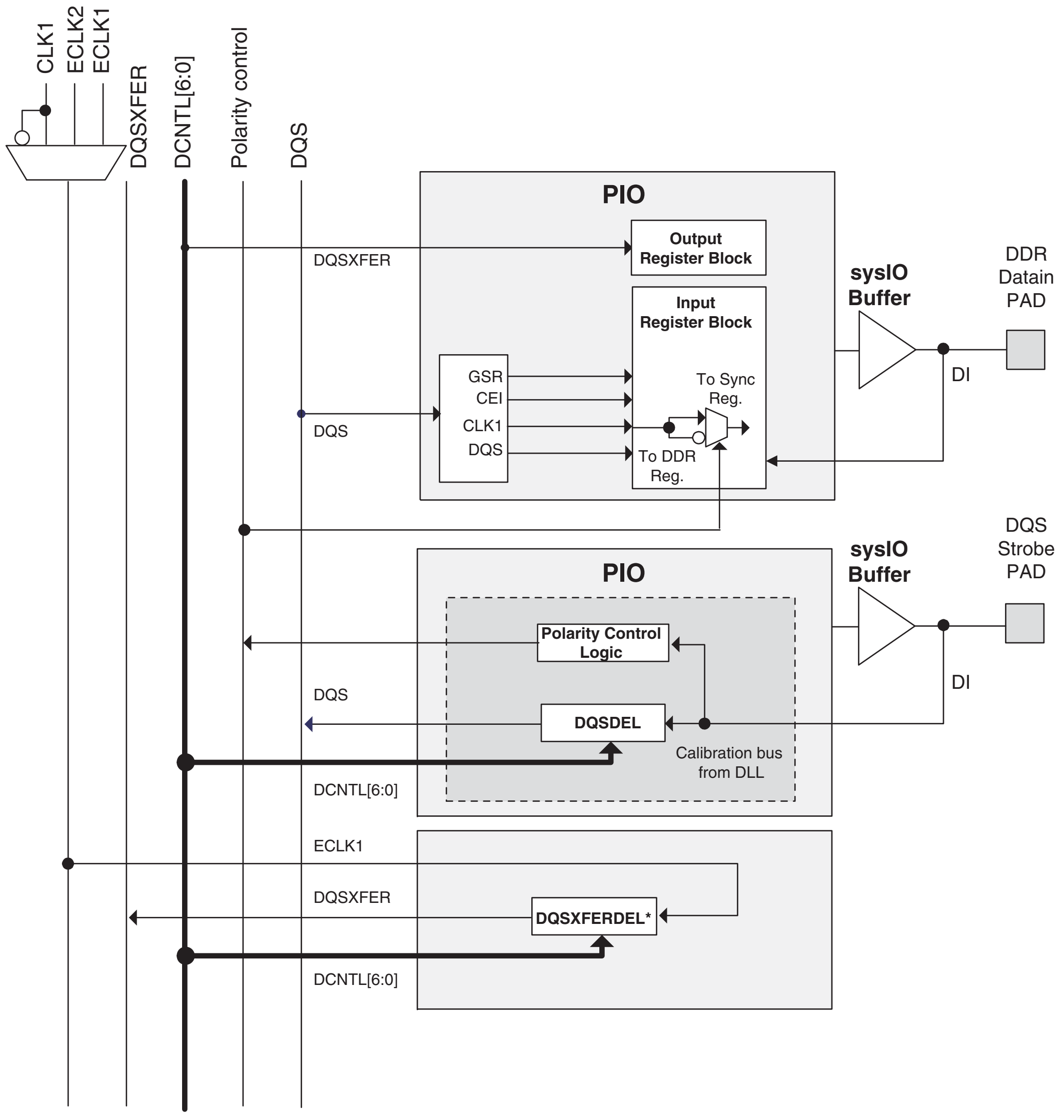
The input register blocks for PIOs contain delay elements and registers that can be used to condition high-speed interface signals, such as DDR memory interfaces and source synchronous interfaces, before they are passed to the device core. Figure 2-26 shows the diagram of the input register block.

Input signals are fed from the sysIO buffer to the input register block (as signal DI). If desired, the input signal can bypass the register and delay elements and be used directly as a combinatorial signal (INDD), a clock (INCK) and, in selected blocks, the input to the DQS delay block. If an input delay is desired, designers can select either a fixed delay or a dynamic delay DEL[3:0]. The delay, if selected, reduces input register hold time requirements when using a global clock.

The input block allows three modes of operation. In the Single Data Rate (SDR) mode, the data is registered, by one of the registers in the SDR Sync register block, with the system clock. In DDR mode two registers are used to sample the data on the positive and negative edges of the DQS signal which creates two data streams, D0 and D2. D0 and D2 are synchronized with the system clock before entering the core. Further information on this topic can be found in the DDR Memory Support section of this data sheet.

By combining input blocks of the complementary PIOs and sharing registers from output blocks, a gearbox function can be implemented, that takes a double data rate signal applied to PIOA and converts it as four data streams, IPOS0A, IPOS1A, IPOS0B and IPOS1B. Figure 2-26 shows the diagram using this gearbox function. For more information on this topic, please see TN1138, LatticeXP2 High Speed I/O Interface.

Figure 2-31. DQS Local Bus



*DQSXFERDEL shifts ECLK1 by 90% and is not associated with a particular PIO.

Polarity Control Logic

In a typical DDR memory interface design, the phase relationship between the incoming delayed DQS strobe and the internal system clock (during the READ cycle) is unknown. The LatticeXP2 family contains dedicated circuits to transfer data between these domains. To prevent set-up and hold violations, at the domain transfer between DQS (delayed) and the system clock, a clock polarity selector is used. This changes the edge on which the data is registered in the synchronizing registers in the input register block and requires evaluation at the start of each READ cycle for the correct clock polarity.

Prior to the READ operation in DDR memories, DQS is in tristate (pulled by termination). The DDR memory device drives DQS low at the start of the preamble state. A dedicated circuit detects this transition. This signal is used to control the polarity of the clock to the synchronizing registers.

Absolute Maximum Ratings[1, 2, 3]

Supply Voltage V_{CC} . . . . -0.5 to 1.32V

Supply Voltage V_{CCAUX} . . . . -0.5 to 3.75V

Supply Voltage V_{CCJ} . . . . -0.5 to 3.75V

Supply Voltage V_{CCPLL}[4] . . . . -0.5 to 3.75V

Output Supply Voltage V_{CCIO} . . . . -0.5 to 3.75V

Input or I/O Tristate Voltage Applied[5] . . . . . . -0.5 to 3.75V

Storage Temperature (Ambient) . . . . -65 to 150°C

Junction Temperature Under Bias (Tj) . . . . +125°C

1. Stress above those listed under the “Absolute Maximum Ratings” may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.
2. Compliance with the Lattice Thermal Management document is required.
3. All voltages referenced to GND.
4. V_{CCPLL} only available on csBGA, PQFP and TQFP packages.
5. Overshoot and undershoot of -2V to (V_{IHMAX} + 2) volts is permitted for a duration of <20 ns.

Recommended Operating Conditions

Symbol	Parameter	Min.	Max.	Units
V_{CC}	Core Supply Voltage	1.14	1.26	V
V_{CCAUX}[4, 5]	Auxiliary Supply Voltage	3.135	3.465	V
V_{CCPLL}[1]	PLL Supply Voltage	3.135	3.465	V
V_{CCIO}[2, 3, 4]	I/O Driver Supply Voltage	1.14	3.465	V
V_{CCJ}[2]	Supply Voltage for IEEE 1149.1 Test Access Port	1.14	3.465	V
t_{JCOM}	Junction Temperature, Commercial Operation	0	85	°C
t_{JIND}	Junction Temperature, Industrial Operation	-40	100	°C

1. V_{CCPLL} only available on csBGA, PQFP and TQFP packages.
2. If V_{CCIO} or V_{CCJ} is set to 1.2 V, they must be connected to the same power supply as V_{CC}. If V_{CCIO} or V_{CCJ} is set to 3.3V, they must be connected to the same power supply as V_{CCAUX}.
3. See recommended voltages by I/O standard in subsequent table.
4. To ensure proper I/O behavior, V_{CCIO} must be turned off at the same time or earlier than V_{CCAUX}.
5. In fpBGA and ftBGA packages, the PLLs are connected to, and powered from, the auxiliary power supply.

On-Chip Flash Memory Specifications

Symbol	Parameter	Max.	Units
$N_{PROGCYC}$	Flash Programming Cycles per $t_{RETENTION}$[1]	10,000	Cycles
	Flash Functional Programming Cycles	100,000	

1. The minimum data retention, $t_{RETENTION}$, is 20 years.

Programming and Erase Flash Supply Current[1, 2, 3, 4, 5]

Over Recommended Operating Conditions

Symbol	Parameter	Device	Typical (25°C, Max. Supply)[6]	Units
I_{CC}	Core Power Supply Current	XP2-5	17	mA
		XP2-8	21	mA
		XP2-17	28	mA
		XP2-30	36	mA
		XP2-40	50	mA
I_{CCAUX}	Auxiliary Power Supply Current[7]	XP2-5	64	mA
		XP2-8	66	mA
		XP2-17	83	mA
		XP2-30	87	mA
		XP2-40	88	mA
I_{CCPLL}	PLL Power Supply Current (per PLL)		0.1	mA
I_{CCIO}	Bank Power Supply Current (per Bank)		5	mA
I_{CCJ}	V_{CCJ} Power Supply Current[8]		14	mA

1. For further information on supply current, please see TN1139, Power Estimation and Management for LatticeXP2 Devices.
2. Assumes all outputs are tristated, all inputs are configured as LVCMOS and held at the V_{CCIO} or GND.
3. Frequency 0 MHz (excludes dynamic power from FPGA operation).
4. A specific configuration pattern is used that scales with the size of the device; consists of 75% PFU utilization, 50% EBR, and 25% I/O configuration.
5. Bypass or decoupling capacitor across the supply.
6. T_J = 25°C, power supplies at nominal voltage.
7. In fpBGA and ftBGA packages the PLLs are connected to and powered from the auxiliary power supply. For these packages, the actual auxiliary supply current is the sum of I_{CCAUX} and I_{CCPLL}. For csBGA, PQFP and TQFP packages the PLLs are powered independent of the auxiliary power supply.
8. When programming via JTAG.

sysIO Single-Ended DC Electrical Characteristics

Over Recommended Operating Conditions

Input/Output Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}[1] (mA)	I_{OH}[1] (mA)
	Min. (V)	Max. (V)	Min. (V)	Max. (V)	Max. (V)	Min. (V)		
LVCMOS33	-0.3	0.8	2.0	3.6	0.4	V_{CCIO} - 0.4	20, 16, 12, 8, 4	-20, -16, -12, -8, -4
					0.2	V_{CCIO} - 0.2	0.1	-0.1
LVTTL33	-0.3	0.8	2.0	3.6	0.4	V_{CCIO} - 0.4	20, 16, 12, 8, 4	-20, -16, -12, -8, -4
					0.2	V_{CCIO} - 0.2	0.1	-0.1
LVCMOS25	-0.3	0.7	1.7	3.6	0.4	V_{CCIO} - 0.4	20, 16, 12, 8, 4	-20, -16, -12, -8, -4
					0.2	V_{CCIO} - 0.2	0.1	-0.1
LVCMOS18	-0.3	0.35 V_{CCIO}	0.65 V_{CCIO}	3.6	0.4	V_{CCIO} - 0.4	16, 12, 8, 4	-16, -12, -8, -4
					0.2	V_{CCIO} - 0.2	0.1	-0.1
LVCMOS15	-0.3	0.35 V_{CCIO}	0.65 V_{CCIO}	3.6	0.4	V_{CCIO} - 0.4	8, 4	-8, -4
					0.2	V_{CCIO} - 0.2	0.1	-0.1
LVCMOS12	-0.3	0.35 V_{CC}	0.65 V_{CC}	3.6	0.4	V_{CCIO} - 0.4	6, 2	-6, -2
					0.2	V_{CCIO} - 0.2	0.1	-0.1
PCI33	-0.3	0.3 V_{CCIO}	0.5 V_{CCIO}	3.6	0.1 V_{CCIO}	0.9 V_{CCIO}	1.5	-0.5
SSTL33_I	-0.3	V_{REF} - 0.2	V_{REF} + 0.2	3.6	0.7	V_{CCIO} - 1.1	8	-8
SSTL33_II	-0.3	V_{REF} - 0.2	V_{REF} + 0.2	3.6	0.5	V_{CCIO} - 0.9	16	-16
SSTL25_I	-0.3	V_{REF} - 0.18	V_{REF} + 0.18	3.6	0.54	V_{CCIO} - 0.62	7.6	-7.6
							12	-12
SSTL25_II	-0.3	V_{REF} - 0.18	V_{REF} + 0.18	3.6	0.35	V_{CCIO} - 0.43	15.2	-15.2
							20	-20
SSTL18_I	-0.3	V_{REF} - 0.125	V_{REF} + 0.125	3.6	0.4	V_{CCIO} - 0.4	6.7	-6.7
SSTL18_II	-0.3	V_{REF} - 0.125	V_{REF} + 0.125	3.6	0.28	V_{CCIO} - 0.28	8	-8
							11	-11
HSTL15_I	-0.3	V_{REF} - 0.1	V_{REF} + 0.1	3.6	0.4	V_{CCIO} - 0.4	4	-4
							8	-8
HSTL18_I	-0.3	V_{REF} - 0.1	V_{REF} + 0.1	3.6	0.4	V_{CCIO} - 0.4	8	-8
							12	-12
HSTL18_II	-0.3	V_{REF} - 0.1	V_{REF} + 0.1	3.6	0.4	V_{CCIO} - 0.4	16	-16

1. The average DC current drawn by I/Os between GND connections, or between the last GND in an I/O bank and the end of an I/O bank, as shown in the logic signal connections table shall not exceed n * 8mA, where n is the number of I/Os between bank GND connections or between the last GND in a bank and the end of a bank.

LatticeXP2 External Switching Characteristics (Continued)

Over Recommended Operating Conditions

Parameter	Description	Device	-7		-6		-5		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
t_{H_DELPLL}	Clock to Data Hold - PIO Input Register with Input Data Delay	XP2-5	0.00	—	0.00	—	0.00	—	ns
		XP2-8	0.00	—	0.00	—	0.00	—	ns
		XP2-17	0.00	—	0.00	—	0.00	—	ns
		XP2-30	0.00	—	0.00	—	0.00	—	ns
		XP2-40	0.00	—	0.00	—	0.00	—	ns
DDR[2] and DDR2[3] I/O Pin Parameters									
t_{DVADQ}	Data Valid After DQS (DDR Read)	XP2	—	0.29	—	0.29	—	0.29	UI
t_{DVEDQ}	Data Hold After DQS (DDR Read)	XP2	0.71	—	0.71	—	0.71	—	UI
t_{DQVBS}	Data Valid Before DQS	XP2	0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Data Valid After DQS	XP2	0.25	—	0.25	—	0.25	—	UI
f_{MAX_DDR}	DDR Clock Frequency	XP2	95	200	95	166	95	133	MHz
f_{MAX_DDR2}	DDR Clock Frequency	XP2	133	200	133	200	133	166	MHz
Primary Clock									
f_{MAX_PRI}	Frequency for Primary Clock Tree	XP2	—	420	—	357	—	311	MHz
t_{W_PRI}	Clock Pulse Width for Primary Clock	XP2	1	—	1	—	1	—	ns
t_{SKEW_PRI}	Primary Clock Skew Within a Bank	XP2	—	160	—	160	—	160	ps
Edge Clock (ECLK1 and ECLK2)									
f_{MAX_ECLK}	Frequency for Edge Clock	XP2	—	420	—	357	—	311	MHz
t_{W_ECLK}	Clock Pulse Width for Edge Clock	XP2	1	—	1	—	1	—	ns
t_{SKEW_ECLK}	Edge Clock Skew Within an Edge of the Device	XP2	—	130	—	130	—	130	ps

1. General timing numbers based on LVCMOS 2.5, 12mA, 0pf load.
2. DDR timing numbers based on SSTL25.
3. DDR2 timing numbers based on SSTL18.

LatticeXP2 Internal Switching Characteristics[1] (Continued)

Over Recommended Operating Conditions

Parameter	Description	-7		-6		-5		Units
		Min.	Max.	Min.	Max.	Min.	Max.	
t_{RST_PIO}	Asynchronous reset time for PFU Logic	—	0.386	—	0.419	—	0.452	ns
t_{DEL}	Dynamic Delay Step Size	0.035	0.035	0.035	0.035	0.035	0.035	ns
EBR Timing								
t_{CO_EBR}	Clock (Read) to Output from Address or Data	—	2.774	—	3.142	—	3.510	ns
t_{COO_EBR}	Clock (Write) to Output from EBR Output Register	—	0.360	—	0.408	—	0.456	ns
t_{SUDATA_EBR}	Setup Data to EBR Memory (Write Clk)	-0.167	—	-0.198	—	-0.229	—	ns
t_{HDATA_EBR}	Hold Data to EBR Memory (Write Clk)	0.194	—	0.231	—	0.267	—	ns
t_{SUADDR_EBR}	Setup Address to EBR Memory (Write Clk)	-0.117	—	-0.137	—	-0.157	—	ns
t_{HADDR_EBR}	Hold Address to EBR Memory (Write Clk)	0.157	—	0.182	—	0.207	—	ns
t_{SUWREN_EBR}	Setup Write/Read Enable to EBR Memory (Write/Read Clk)	-0.135	—	-0.159	—	-0.182	—	ns
t_{HWREN_EBR}	Hold Write/Read Enable to EBR Memory (Write/Read Clk)	0.158	—	0.186	—	0.214	—	ns
t_{SUCE_EBR}	Clock Enable Setup Time to EBR Output Register (Read Clk)	0.144	—	0.160	—	0.176	—	ns
t_{HCE_EBR}	Clock Enable Hold Time to EBR Output Register (Read Clk)	-0.097	—	-0.113	—	-0.129	—	ns
t_{RSTO_EBR}	Reset To Output Delay Time from EBR Output Register (Asynchronous)	—	1.156	—	1.341	—	1.526	ns
t_{SUBE_EBR}	Byte Enable Set-Up Time to EBR Output Register	-0.117	—	-0.137	—	-0.157	—	ns
t_{HBE_EBR}	Byte Enable Hold Time to EBR Output Register Dynamic Delay on Each PIO	0.157	—	0.182	—	0.207	—	ns
t_{RSTREC_EBR}	Asynchronous reset recovery time for EBR	0.233	—	0.291	—	0.347	—	ns
t_{RST_EBR}	Asynchronous reset time for EBR	—	1.156	—	1.341	—	1.526	ns
PLL Parameters								
$t_{RSTKREC\_PLL}$	After RSTK De-assert, Recovery Time Before Next Clock Edge Can Toggle K-divider Counter	1.000	—	1.000	—	1.000	—	ns
t_{RSTREC_PLL}	After RST De-assert, Recovery Time Before Next Clock Edge Can Toggle M-divider Counter (Applies to M-Divider Portion of RST Only[2])	1.000	—	1.000	—	1.000	—	ns
DSP Block Timing								
t_{SUI_DSP}	Input Register Setup Time	0.135	—	0.151	—	0.166	—	ns
t_{HI_DSP}	Input Register Hold Time	0.021	—	-0.006	—	-0.031	—	ns
t_{SUP_DSP}	Pipeline Register Setup Time	2.505	—	2.784	—	3.064	—	ns

LatticeXP2 Internal Switching Characteristics[1] (Continued)

Over Recommended Operating Conditions

Parameter	Description	-7		-6		-5		Units
		Min.	Max.	Min.	Max.	Min.	Max.	
t_{HP_DSP}	Pipeline Register Hold Time	-0.787	—	-0.890	—	-0.994	—	ns
t_{SUO_DSP}	Output Register Setup Time	4.896	—	5.413	—	5.931	—	ns
t_{HO_DSP}	Output Register Hold Time	-1.439	—	-1.604	—	-1.770	—	ns
t_{COI_DSP}[3]	Input Register Clock to Output Time	—	4.513	—	4.947	—	5.382	ns
t_{COP_DSP}[3]	Pipeline Register Clock to Output Time	—	2.153	—	2.272	—	2.391	ns
t_{COO_DSP}[3]	Output Register Clock to Output Time	—	0.569	—	0.600	—	0.631	ns
$t_{SUADSUB}$	AdSub Input Register Setup Time	-0.270	—	-0.298	—	-0.327	—	ns
t_{HADSUB}	AdSub Input Register Hold Time	0.306	—	0.338	—	0.371	—	ns

1. Internal parameters are characterized, but not tested on every device.
2. RST resets VCO and all counters in PLL.
3. These parameters include the Adder Subtractor block in the path.

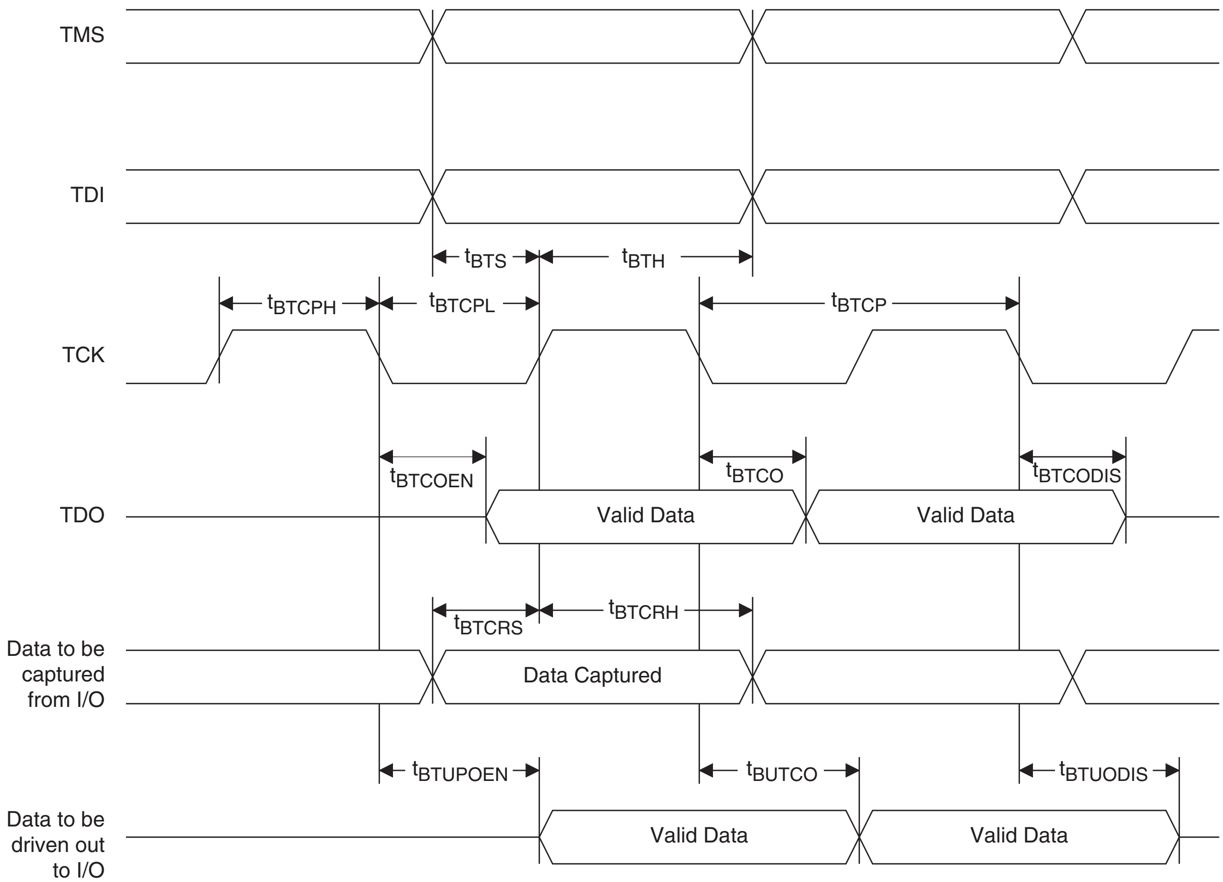
LatticeXP2 Family Timing Adders[1, 2, 3, 4] (Continued)

Over Recommended Operating Conditions

Buffer Type	Description	-7	-6	-5	Units
LVCMOS25_4mA	LVCMOS 2.5 4mA drive, slow slew rate	1.05	1.43	1.81	ns
LVCMOS25_8mA	LVCMOS 2.5 8mA drive, slow slew rate	0.78	1.15	1.52	ns
LVCMOS25_12mA	LVCMOS 2.5 12mA drive, slow slew rate	0.59	0.96	1.33	ns
LVCMOS25_16mA	LVCMOS 2.5 16mA drive, slow slew rate	0.81	1.18	1.55	ns
LVCMOS25_20mA	LVCMOS 2.5 20mA drive, slow slew rate	0.61	0.98	1.35	ns
LVCMOS18_4mA	LVCMOS 1.8 4mA drive, slow slew rate	1.01	1.38	1.75	ns
LVCMOS18_8mA	LVCMOS 1.8 8mA drive, slow slew rate	0.72	1.08	1.45	ns
LVCMOS18_12mA	LVCMOS 1.8 12mA drive, slow slew rate	0.53	0.90	1.26	ns
LVCMOS18_16mA	LVCMOS 1.8 16mA drive, slow slew rate	0.74	1.11	1.48	ns
LVCMOS15_4mA	LVCMOS 1.5 4mA drive, slow slew rate	0.96	1.33	1.71	ns
LVCMOS15_8mA	LVCMOS 1.5 8mA drive, slow slew rate	-0.53	-0.26	0.00	ns
LVCMOS12_2mA	LVCMOS 1.2 2mA drive, slow slew rate	0.90	1.27	1.65	ns
LVCMOS12_6mA	LVCMOS 1.2 6mA drive, slow slew rate	-0.55	-0.29	-0.02	ns
PCI33	3.3V PCI	-0.29	-0.01	0.26	ns

1. Timing Adders are characterized but not tested on every device.
2. LVCMOS timing measured with the load specified in Switching Test Condition table.
3. All other standards tested according to the appropriate specifications.
4. The base parameters used with these timing adders to calculate timing are listed in the LatticeXP2 Internal Switching Characteristics table under PIO Input/Output Timing.
5. These timing adders are measured with the recommended resistor values.

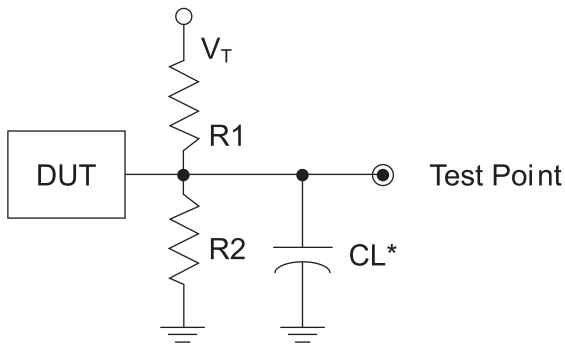
Figure 3-10. JTAG Port Timing Waveforms



Switching Test Conditions

Figure 3-11 shows the output test load that is used for AC testing. The specific values for resistance, capacitance, voltage, and other test conditions are shown in Table 3-6.

Figure 3-11. Output Test Load, LVTTL and LVCMOS Standards



*CL Includes Test Fixture and Probe Capacitance

Table 3-6. Test Fixture Required Components, Non-Terminated Interfaces

Test Condition	R_1	R_2	C_L	Timing Ref.	V_T
LVTTL and other LVCMOS settings (L -> H, H -> L)	∞	∞	0pF	LVCMOS 3.3 = 1.5V	—
				LVCMOS 2.5 = $V_{CCIO}/2$	—
				LVCMOS 1.8 = $V_{CCIO}/2$	—
				LVCMOS 1.5 = $V_{CCIO}/2$	—
				LVCMOS 1.2 = $V_{CCIO}/2$	—
LVCMOS 2.5 I/O (Z -> H)	∞	1MΩ		$V_{CCIO}/2$	—
LVCMOS 2.5 I/O (Z -> L)	1MΩ	∞		$V_{CCIO}/2$	V_{CCIO}
LVCMOS 2.5 I/O (H -> Z)	∞	100		V_{OH} - 0.10	—
LVCMOS 2.5 I/O (L -> Z)	100	∞		V_{OL} + 0.10	V_{CCIO}

Note: Output test conditions for all other interfaces are determined by the respective standards.

PICs and DDR Data (DQ) Pins Associated with the DDR Strobe (DQS) Pin

PICs Associated with DQS Strobe	PIO Within PIC	DDR Strobe (DQS) and Data (DQ) Pins
For Left and Right Edges of the Device		
P[Edge] [n-4]	A	DQ
	B	DQ
P[Edge] [n-3]	A	DQ
	B	DQ
P[Edge] [n-2]	A	DQ
	B	DQ
P[Edge] [n-1]	A	DQ
	B	DQ
P[Edge] [n]	A	[Edge]DQSn
	B	DQ
P[Edge] [n+1]	A	DQ
	B	DQ
P[Edge] [n+2]	A	DQ
	B	DQ
P[Edge] [n+3]	A	DQ
	B	DQ
For Top and Bottom Edges of the Device		
P[Edge] [n-4]	A	DQ
	B	DQ
P[Edge] [n-3]	A	DQ
	B	DQ
P[Edge] [n-2]	A	DQ
	B	DQ
P[Edge] [n-1]	A	DQ
	B	DQ
P[Edge] [n]	A	[Edge]DQSn
	B	DQ
P[Edge] [n+1]	A	DQ
	B	DQ
P[Edge] [n+2]	A	DQ
	B	DQ
P[Edge] [n+3]	A	DQ
	B	DQ
P[Edge] [n+4]	A	DQ
	B	DQ

Notes:
1. “n” is a row PIC number.
2. The DDR interface is designed for memories that support one DQS strobe up to 16 bits of data for the left and right edges and up to 18 bits of data for the top and bottom edges. In some packages, all the potential DDR data (DQ) pins may not be available. PIC numbering definitions are provided in the “Signal Names” column of the Signal Descriptions table.

Lead-Free Packaging

Commercial

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-5E-5MN132C	1.2V	-5	Lead-Free csBGA	132	COM	5
LFXP2-5E-6MN132C	1.2V	-6	Lead-Free csBGA	132	COM	5
LFXP2-5E-7MN132C	1.2V	-7	Lead-Free csBGA	132	COM	5
LFXP2-5E-5TN144C	1.2V	-5	Lead-Free TQFP	144	COM	5
LFXP2-5E-6TN144C	1.2V	-6	Lead-Free TQFP	144	COM	5
LFXP2-5E-7TN144C	1.2V	-7	Lead-Free TQFP	144	COM	5
LFXP2-5E-5QN208C	1.2V	-5	Lead-Free PQFP	208	COM	5
LFXP2-5E-6QN208C	1.2V	-6	Lead-Free PQFP	208	COM	5
LFXP2-5E-7QN208C	1.2V	-7	Lead-Free PQFP	208	COM	5
LFXP2-5E-5FTN256C	1.2V	-5	Lead-Free ftBGA	256	COM	5
LFXP2-5E-6FTN256C	1.2V	-6	Lead-Free ftBGA	256	COM	5
LFXP2-5E-7FTN256C	1.2V	-7	Lead-Free ftBGA	256	COM	5

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-8E-5MN132C	1.2V	-5	Lead-Free csBGA	132	COM	8
LFXP2-8E-6MN132C	1.2V	-6	Lead-Free csBGA	132	COM	8
LFXP2-8E-7MN132C	1.2V	-7	Lead-Free csBGA	132	COM	8
LFXP2-8E-5TN144C	1.2V	-5	Lead-Free TQFP	144	COM	8
LFXP2-8E-6TN144C	1.2V	-6	Lead-Free TQFP	144	COM	8
LFXP2-8E-7TN144C	1.2V	-7	Lead-Free TQFP	144	COM	8
LFXP2-8E-5QN208C	1.2V	-5	Lead-Free PQFP	208	COM	8
LFXP2-8E-6QN208C	1.2V	-6	Lead-Free PQFP	208	COM	8
LFXP2-8E-7QN208C	1.2V	-7	Lead-Free PQFP	208	COM	8
LFXP2-8E-5FTN256C	1.2V	-5	Lead-Free ftBGA	256	COM	8
LFXP2-8E-6FTN256C	1.2V	-6	Lead-Free ftBGA	256	COM	8
LFXP2-8E-7FTN256C	1.2V	-7	Lead-Free ftBGA	256	COM	8

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-17E-5QN208C	1.2V	-5	Lead-Free PQFP	208	COM	17
LFXP2-17E-6QN208C	1.2V	-6	Lead-Free PQFP	208	COM	17
LFXP2-17E-7QN208C	1.2V	-7	Lead-Free PQFP	208	COM	17
LFXP2-17E-5FTN256C	1.2V	-5	Lead-Free ftBGA	256	COM	17
LFXP2-17E-6FTN256C	1.2V	-6	Lead-Free ftBGA	256	COM	17
LFXP2-17E-7FTN256C	1.2V	-7	Lead-Free ftBGA	256	COM	17
LFXP2-17E-5FN484C	1.2V	-5	Lead-Free fpBGA	484	COM	17
LFXP2-17E-6FN484C	1.2V	-6	Lead-Free fpBGA	484	COM	17
LFXP2-17E-7FN484C	1.2V	-7	Lead-Free fpBGA	484	COM	17

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-40E-5F484C	1.2V	-5	fpBGA	484	COM	40
LFXP2-40E-6F484C	1.2V	-6	fpBGA	484	COM	40
LFXP2-40E-7F484C	1.2V	-7	fpBGA	484	COM	40
LFXP2-40E-5F672C	1.2V	-5	fpBGA	672	COM	40
LFXP2-40E-6F672C	1.2V	-6	fpBGA	672	COM	40
LFXP2-40E-7F672C	1.2V	-7	fpBGA	672	COM	40

Industrial

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-5E-5M132I	1.2V	-5	csBGA	132	IND	5
LFXP2-5E-6M132I	1.2V	-6	csBGA	132	IND	5
LFXP2-5E-6FT256I	1.2V	-6	ftBGA	256	IND	5

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-8E-5M132I	1.2V	-5	csBGA	132	IND	8
LFXP2-8E-6M132I	1.2V	-6	csBGA	132	IND	8
LFXP2-5E-5FT256I	1.2V	-5	ftBGA	256	IND	5
LFXP2-8E-5FT256I	1.2V	-5	ftBGA	256	IND	8
LFXP2-8E-6FT256I	1.2V	-6	ftBGA	256	IND	8

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-17E-5FT256I	1.2V	-5	ftBGA	256	IND	17
LFXP2-17E-6FT256I	1.2V	-6	ftBGA	256	IND	17
LFXP2-17E-5F484I	1.2V	-5	fpBGA	484	IND	17
LFXP2-17E-6F484I	1.2V	-6	fpBGA	484	IND	17

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (k)
LFXP2-30E-5FT256I	1.2V	-5	ftBGA	256	IND	30
LFXP2-30E-6FT256I	1.2V	-6	ftBGA	256	IND	30
LFXP2-30E-5F484I	1.2V	-5	fpBGA	484	IND	30
LFXP2-30E-6F484I	1.2V	-6	fpBGA	484	IND	30
LFXP2-30E-5F672I	1.2V	-5	fpBGA	672	IND	30
LFXP2-30E-6F672I	1.2V	-6	fpBGA	672	IND	30

Date	Version	Section	Change Summary
April 2008 (cont.)	01.4 (cont.)	DC and Switching Characteristics (cont.)	Updated Flash Download Time (From On-Chip Flash to SRAM) Table
			Updated Flash Program Time Table
			Updated Flash Erase Time Table
			Updated FlashBAK (from EBR to Flash) Table
			Updated Hot Socketing Specifications Table footnotes
		Pinout Information	Updated Signal Descriptions Table
June 2008	01.5	Architecture	Removed Read-Before-Write sysMEM EBR mode.
			Clarification of the operation of the secondary clock regions.
		DC and Switching Characteristics	Removed Read-Before-Write sysMEM EBR mode.
		Pinout Information	Updated DDR Banks Bonding Out per I/O Bank section of Pin Information Summary Table.
August 2008	01.6	—	Data sheet status changed from preliminary to final.
		Architecture	Clarification of the operation of the secondary clock regions.
		DC and Switching Characteristics	Removed “8W” specification from Hot Socketing Specifications table.
			Removed "8W" footnote from DC Electrical Characteristics table.
			Updated Register-to-Register Performance table.
		Ordering Information	Removed “8W” option from Part Number Description.
			Removed XP2-17 “8W” OPNs.
April 2011	01.7	DC and Switching Characteristics	Recommended Operating Conditions table, added footnote 5.
			On-Chip Flash Memory Specifications table, added footnote 1.
			BLVDS DC Conditions, corrected column title to be Z0 = 90 ohms.
			sysCONFIG Port Timing Specifications table, added footnote 1 for t_{DINIT}.
January 2012	01.8	Multiple	Added support for Lattice Diamond design software.
		Architecture	Corrected information regarding SED support.
		DC and Switching Characteristics	Added reference to ESD Performance Qualification Summary information.
May 2013	01.9	All	Updated document with new corporate logo.
		Architecture	Architecture Overview – Added information on the state of the register on power up and after configuration.
			Added information regarding SED support.
		DC and Switching Characteristics	Removed Input Clock Rise/Fall Time 1ns max from the sysCLOCK PLL Timing table.
		Ordering Information	Updated topside mark in Ordering Information diagram.
March 2014	02.0	Architecture	Updated Typical sysIO I/O Behavior During Power-up section. Added information on POR signal deactivation.
August 2014	02.1	Architecture	Updated Typical sysIO I/O Behavior During Power-up section. Described user I/Os during power up and before FPGA core logic is active.
September 2014	2.2	DC and Switching Characteristics	Updated Switching Test Conditions section. Re-linked missing figure.